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Understanding <u>Embedded - FPGAs (Field</u> <u>Programmable Gate Array)</u>

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	1536
Total RAM Bits	18432
Number of I/O	71
Number of Gates	60000
Voltage - Supply	1.14V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	100-TQFP
Supplier Device Package	100-VQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/agl060v2-vq100

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1 – IGLOO Device Family Overview

General Description

The IGLOO family of flash FPGAs, based on a 130-nm flash process, offers the lowest power FPGA, a single-chip solution, small footprint packages, reprogrammability, and an abundance of advanced features.

The Flash*Freeze technology used in IGLOO devices enables entering and exiting an ultra-low power mode that consumes as little as 5 μ W while retaining SRAM and register data. Flash*Freeze technology simplifies power management through I/O and clock management with rapid recovery to operation mode.

The Low Power Active capability (static idle) allows for ultra-low power consumption (from 12 μ W) while the IGLOO device is completely functional in the system. This allows the IGLOO device to control system power management based on external inputs (e.g., scanning for keyboard stimulus) while consuming minimal power.

Nonvolatile flash technology gives IGLOO devices the advantage of being a secure, low power, singlechip solution that is Instant On. IGLOO is reprogrammable and offers time-to-market benefits at an ASIClevel unit cost.

These features enable designers to create high-density systems using existing ASIC or FPGA design flows and tools.

IGLOO devices offer 1 kbit of on-chip, reprogrammable, nonvolatile FlashROM storage as well as clock conditioning circuitry based on an integrated phase-locked loop (PLL). The AGL015 and AGL030 devices have no PLL or RAM support. IGLOO devices have up to 1 million system gates, supported with up to 144 kbits of true dual-port SRAM and up to 300 user I/Os.

M1 IGLOO devices support the high-performance, 32-bit Cortex-M1 processor developed by ARM for implementation in FPGAs. Cortex-M1 is a soft processor that is fully implemented in the FPGA fabric. It has a three-stage pipeline that offers a good balance between low power consumption and speed when implemented in an M1 IGLOO device. The processor runs the ARMv6-M instruction set, has a configurable nested interrupt controller, and can be implemented with or without the debug block. Cortex-M1 is available for free from Microsemi for use in M1 IGLOO FPGAs.

The ARM-enabled devices have ordering numbers that begin with M1AGL and do not support AES decryption.

Flash*Freeze Technology

The IGLOO device offers unique Flash*Freeze technology, allowing the device to enter and exit ultra-low power Flash*Freeze mode. IGLOO devices do not need additional components to turn off I/Os or clocks while retaining the design information, SRAM content, and registers. Flash*Freeze technology is combined with in-system programmability, which enables users to quickly and easily upgrade and update their designs in the final stages of manufacturing or in the field. The ability of IGLOO V2 devices to support a wide range of core voltage (1.2 V to 1.5 V) allows further reduction in power consumption, thus achieving the lowest total system power.

When the IGLOO device enters Flash*Freeze mode, the device automatically shuts off the clocks and inputs to the FPGA core; when the device exits Flash*Freeze mode, all activity resumes and data is retained.

The availability of low power modes, combined with reprogrammability, a single-chip and single-voltage solution, and availability of small-footprint, high pin-count packages, make IGLOO devices the best fit for portable electronics.

Table 2-20 • Different Components Contributing to the Static Power Consumption in IGLOO Devices For IGLOO V2 or V5 Devices, 1.5 V DC Core Supply Voltage

				Device-	Specific S	tatic Powe	er (mW)		
Parameter	Definition	AGL1000	AGL600	AGL400	AGL250	AGL125	AGL060	AGL030	AGL015
PDC1	Array static power in Active mode			See	Table 2-12	2 on page 2	2-9.		
PDC2	Array static power in Static (Idle) mode			See	Table 2-11	on page 2	2-8.		
PDC3	Array static power in Flash*Freeze mode			See	e Table 2-9	on page 2	-7.		
PDC4	Static PLL contribution				1.8	34			
PDC5	Bank quiescent power (V _{CCI} -dependent)			See	Table 2-12	2 on page 2	2-9.		
PDC6	I/O input pin static power (standard-dependent)		See Table	2-13 on pa	ige 2-10 th	rough Table	e 2-15 on p	age 2-11.	
PDC7	I/O output pin static power (standard-dependent)		See Table	2-16 on pa	ige 2-11 thi	ough Table	e 2-18 on p	age 2-12.	

Note: *For a different output load, drive strength, or slew rate, Microsemi recommends using the Microsemi power spreadsheet calculator or SmartPower tool in Libero SoC.

Guidelines

Toggle Rate Definition

A toggle rate defines the frequency of a net or logic element relative to a clock. It is a percentage. If the toggle rate of a net is 100%, this means that this net switches at half the clock frequency. Below are some examples:

- The average toggle rate of a shift register is 100% because all flip-flop outputs toggle at half of the clock frequency.
- The average toggle rate of an 8-bit counter is 25%:
 - Bit 0 (LSB) = 100%
 - Bit 1 = 50%
 - Bit 2 = 25%
 - ...
 - Bit 7 (MSB) = 0.78125%
 - Average toggle rate = (100% + 50% + 25% + 12.5% + . . . + 0.78125%) / 8

Enable Rate Definition

Output enable rate is the average percentage of time during which tristate outputs are enabled. When nontristate output buffers are used, the enable rate should be 100%.

Table 2-23 • Toggle Rate Guidelines Recommended for Power Calculation

Component	Definition	Guideline
α ₁	Toggle rate of VersaTile outputs	10%
α ₂	I/O buffer toggle rate	10%

Table 2-24 • Enable Rate Guidelines Recommended for Power Calculation

Component	Definition	Guideline
β ₁	I/O output buffer enable rate	100%
β ₂	RAM enable rate for read operations	12.5%
β ₃	RAM enable rate for write operations	12.5%

2.5 V LVCMOS

Low-Voltage CMOS for 2.5 V is an extension of the LVCMOS standard (JESD8-5) used for general-purpose 2.5 V applications.

2.5 V LVCMOS	v	1L	v	IH	VOL	VОН	IOL	юн	IOSH	IOSL	IIL ¹	IIH ²
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ³	Max. mA ³	μA ⁴	μA ⁴
2 mA	-0.3	0.7	1.7	2.7	0.7	1.7	2	2	16	18	10	10
4 mA	-0.3	0.7	1.7	2.7	0.7	1.7	4	4	16	18	10	10
6 mA	-0.3	0.7	1.7	2.7	0.7	1.7	6	6	32	37	10	10
8 mA	-0.3	0.7	1.7	2.7	0.7	1.7	8	8	32	37	10	10
12 mA	-0.3	0.7	1.7	2.7	0.7	1.7	12	12	65	74	10	10
16 mA	-0.3	0.7	1.7	2.7	0.7	1.7	16	16	83	87	10	10
24 mA	-0.3	0.7	1.7	2.7	0.7	1.7	24	24	169	124	10	10

Table 2-79 • Minimum and Maximum DC Input and Output Levels Applicable to Advanced I/O Banks

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where -0.3 V < VIN < VIL.

2. IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges

3. Currents are measured at 100°C junction temperature and maximum voltage.

4. Currents are measured at 85°C junction temperature.

5. Software default selection highlighted in gray.

 Table 2-80 •
 Minimum and Maximum DC Input and Output Levels

 Applicable to Standard Plus I/O Banks

2.5 V LVCMOS	v	ΊL	v	ΊH	VOL	vон	IOL	юн	IOSH	IOSL	IIL ¹	IIH ²
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ³	Max. mA ³	μA ⁴	μA ⁴
2 mA	-0.3	0.7	1.7	2.7	0.7	1.7	2	2	16	18	10	10
4 mA	-0.3	0.7	1.7	2.7	0.7	1.7	4	4	16	18	10	10
6 mA	-0.3	0.7	1.7	2.7	0.7	1.7	6	6	32	37	10	10
8 mA	-0.3	0.7	1.7	2.7	0.7	1.7	8	8	32	37	10	10
12 mA	-0.3	0.7	1.7	2.7	0.7	1.7	12	12	65	74	10	10

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.

2. IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges

3. Currents are measured at 100°C junction temperature and maximum voltage.

4. Currents are measured at 85°C junction temperature.

5. Software default selection highlighted in gray.

Applies to 1.2 V Core Voltage

Table 2-89 • 2.5 V LVCMOS Low Slew – Applies to 1.2 V DC Core Voltage Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 2.3 V Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{ZHS}	Units
2 mA	Std.	1.55	5.59	0.26	1.20	1.10	5.68	5.14	2.82	2.80	11.47	10.93	ns
4 mA	Std.	1.55	5.59	0.26	1.20	1.10	5.68	5.14	2.82	2.80	11.47	10.93	ns
6 mA	Std.	1.55	4.76	0.26	1.20	1.10	4.84	4.47	3.10	3.33	10.62	10.26	ns
8 mA	Std.	1.55	4.76	0.26	1.20	1.10	4.84	4.47	3.10	3.33	10.62	10.26	ns
12 mA	Std.	1.55	4.17	0.26	1.20	1.10	4.23	3.99	3.30	3.67	10.02	9.77	ns
16 mA	Std.	1.55	3.98	0.26	1.20	1.10	4.04	3.88	3.34	3.76	9.83	9.66	ns
24 mA	Std.	1.55	3.90	0.26	1.20	1.10	3.96	3.90	3.40	4.09	9.75	9.68	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-90 • 2.5 V LVCMOS High Slew – Applies to 1.2 V DC Core Voltage

Commercial-Case Conditions: $T_J = 70^{\circ}$ C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 2.3 V Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{zHS}	Units
2 mA	Std.	1.55	3.33	0.26	1.20	1.10	3.38	3.09	2.82	2.91	9.17	8.88	ns
4 mA	Std.	1.55	3.33	0.26	1.20	1.10	3.38	3.09	2.82	2.91	9.17	8.88	ns
6 mA	Std.	1.55	2.89	0.26	1.20	1.10	2.93	2.56	3.10	3.45	8.72	8.34	ns
8 mA	Std.	1.55	2.89	0.26	1.20	1.10	2.93	2.56	3.10	3.45	8.72	8.34	ns
12 mA	Std.	1.55	2.64	0.26	1.20	1.10	2.67	2.29	3.30	3.79	8.46	8.08	ns
16 mA	Std.	1.55	2.59	0.26	1.20	1.10	2.63	2.24	3.34	3.88	8.41	8.03	ns
24 mA	Std.	1.55	2.60	0.26	1.20	1.10	2.64	2.18	3.40	4.22	8.42	7.97	ns

Notes:

1. Software default selection highlighted in gray.

2. For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-91 • 2.5 V LVCMOS Low Slew – Applies to 1.2 V DC Core Voltage Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 2.3 V Applicable to Standard Plus Banks

Drive Strength	Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{ZHS}	Units
2 mA	Std.	1.55	5.02	0.26	1.19	1.10	5.11	4.60	2.50	2.62	10.89	10.38	ns
4 mA	Std.	1.55	5.02	0.26	1.19	1.10	5.11	4.60	2.50	2.62	10.89	10.38	ns
6 mA	Std.	1.55	4.21	0.26	1.19	1.10	4.27	4.00	2.76	3.10	10.06	9.79	ns
8 mA	Std.	1.55	4.21	0.26	1.19	1.10	4.27	4.00	2.76	3.10	10.06	9.79	ns
12 mA	Std.	1.55	3.66	0.26	1.19	1.10	3.71	3.55	2.94	3.41	9.50	9.34	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-107 • 1.8 V LVCMOS Low Slew – Applies to 1.2 V DC Core VoltageCommercial-Case Conditions: TJ = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.7 VApplicable to Standard Plus Banks

Drive Strength	Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{zHS}	Units
2 mA	Std.	1.55	6.32	0.26	1.11	1.10	6.43	5.81	2.47	2.16	12.22	11.60	ns
4 mA	Std.	1.55	5.27	0.26	1.11	1.10	5.35	5.01	2.78	2.92	11.14	10.79	ns
6 mA	Std.	1.55	4.56	0.26	1.11	1.10	4.64	4.44	3.00	3.30	10.42	10.22	ns
8 mA	Std.	1.55	4.56	0.26	1.11	1.10	4.64	4.44	3.00	3.30	10.42	10.22	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-108 • 1.8 V LVCMOS High Slew – Applies to 1.2 V DC Core Voltage

Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.7 V Applicable to Standard Plus Banks

Drive Strength	Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{zHS}	Units
2 mA	Std.	1.55	3.22	0.26	1.11	1.10	3.26	3.18	2.47	2.20	9.05	8.97	ns
4 mA	Std.	1.55	2.72	0.26	1.11	1.10	2.75	2.50	2.78	3.01	8.54	8.29	ns
6 mA	Std.	1.55	2.43	0.26	1.11	1.10	2.47	2.16	2.99	3.39	8.25	7.94	ns
8 mA	Std.	1.55	2.43	0.26	1.11	1.10	2.47	2.16	2.99	3.39	8.25	7.94	ns

Notes:

1. Software default selection highlighted in gray.

2. For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-109 • 1.8 V LVCMOS Low Slew – Applies to 1.2 V DC Core Voltage

Commercial-Case Conditions: $T_J = 70^{\circ}$ C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.7 V Applicable to Standard Banks

Drive Strength	Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	Units
2 mA	Std.	1.55	6.13	0.26	1.08	1.10	6.24	5.79	2.08	1.78	ns
4 mA	Std.	1.55	5.17	0.26	1.08	1.10	5.26	4.98	2.38	2.54	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-110 • 1.8 V LVCMOS High Slew – Applies to 1.2 V DC Core Voltage

Commercial-Case Conditions: $T_J = 70^{\circ}$ C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.7 V Applicable to Standard Banks

Drive Strength	Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	Units
2 mA	Std.	3.06	0.26	1.08	1.10	3.10	3.01	2.08	1.83	3.06	ns
4 mA	Std.	2.60	0.26	1.08	1.10	2.64	2.33	2.38	2.62	2.60	ns

Notes:

1. Software default selection highlighted in gray.

2. For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

I/O Register Specifications



Fully Registered I/O Buffers with Synchronous Enable and Asynchronous Preset

Figure 2-16 • Timing Model of Registered I/O Buffers with Synchronous Enable and Asynchronous Preset

DDR Module Specifications

Input DDR Module



Figure 2-21 • Input DDR Timing Model

Table 2-163 •	Parameter	Definitions
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Parameter Name	Parameter Definition	Measuring Nodes (from, to)
t _{DDRICLKQ1}	Clock-to-Out Out_QR	B, D
t _{DDRICLKQ2}	Clock-to-Out Out_QF	B, E
t _{DDRISUD}	Data Setup Time of DDR input	А, В
t _{DDRIHD}	Data Hold Time of DDR input	А, В
t _{DDRICLR2Q1}	Clear-to-Out Out_QR	C, D
t _{DDRICLR2Q2}	Clear-to-Out Out_QF	C, E
t _{DDRIREMCLR}	Clear Removal	С, В
t _{DDRIRECCLR}	Clear Recovery	С, В



Figure 2-30 • Peak-to-Peak Jitter Definition

Timing Characteristics

1.5 V DC Core Voltage

Table 2-191 • RAM4K9

Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

Parameter	Description	Std.	Units
t _{AS}	Address setup time	0.83	ns
t _{AH}	Address hold time	0.16	ns
t _{ENS}	REN, WEN setup time	0.81	ns
t _{ENH}	REN, WEN hold time	0.16	ns
t _{BKS}	BLK setup time	1.65	ns
t _{BKH}	BLK hold time	0.16	ns
t _{DS}	Input data (DIN) setup time	0.71	ns
t _{DH}	Input data (DIN) hold time	0.36	ns
t _{CKQ1}	Clock High to new data valid on DOUT (output retained, WMODE = 0)	3.53	ns
	Clock High to new data valid on DOUT (flow-through, WMODE = 1)	3.06	ns
t _{CKQ2}	Clock High to new data valid on DOUT (pipelined)	1.81	ns
t _{C2CWWL} 1	Address collision clk-to-clk delay for reliable write after write on same address – Applicable to Closing Edge	0.23	ns
t _{C2CRWL} 1	Address collision clk-to-clk delay for reliable read access after write on same address – Applicable to Opening Edge	0.35	ns
t _{C2CWRH} 1	Address collision clk-to-clk delay for reliable write access after read on same address – Applicable to Opening Edge	0.41	ns
t _{RSTBQ}	RESET Low to data out Low on DOUT (flow-through)	2.06	ns
	RESET Low to data out Low on DOUT (pipelined)	2.06	ns
t _{REMRSTB}	RESET removal	0.61	ns
t _{RECRSTB}	RESET recovery	3.21	ns
t _{MPWRSTB}	RESET minimum pulse width	0.68	ns
t _{CYC}	Clock cycle time	6.24	ns
F _{MAX}	Maximum frequency	160	MHz

Notes:

1. For more information, refer to the application note Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs.

2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

1.2 V DC Core Voltage

Table 2-196 • FIFO

Worst Commercial-Case Conditions: $T_J = 70^{\circ}C$, VCC = 1.14 V

Parameter	Description	Std.	Units
t _{ENS}	REN, WEN Setup Time	4.13	ns
t _{ENH}	REN, WEN Hold Time	0.31	ns
t _{BKS}	BLK Setup Time	0.47	ns
t _{BKH}	BLK Hold Time	0.00	ns
t _{DS}	Input Data (WD) Setup Time	1.56	ns
t _{DH}	Input Data (WD) Hold Time	0.49	ns
t _{CKQ1}	Clock High to New Data Valid on RD (flow-through)	6.80	ns
t _{CKQ2}	Clock High to New Data Valid on RD (pipelined)	3.62	ns
t _{RCKEF}	RCLK High to Empty Flag Valid	7.23	ns
t _{WCKFF}	WCLK High to Full Flag Valid	6.85	ns
t _{CKAF}	Clock High to Almost Empty/Full Flag Valid	26.61	ns
t _{RSTFG}	RESET Low to Empty/Full Flag Valid	7.12	ns
t _{RSTAF}	RESET Low to Almost Empty/Full Flag Valid	26.33	ns
t _{RSTBQ}	RESET Low to Data Out Low on RD (flow-through)	4.09	ns
	RESET Low to Data Out Low on RD (pipelined)	4.09	ns
t _{REMRSTB}	RESET Removal	1.23	ns
t _{RECRSTB}	RESET Recovery	6.58	ns
t _{MPWRSTB}	RESET Minimum Pulse Width	1.18	ns
t _{CYC}	Clock Cycle Time	10.90	ns
F _{MAX}	Maximum Frequency for FIFO	92	MHz

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

	CS281	CS281		
Pin Number	AGL600 Function	Pin Number	AGL600 Function	
R15	IO94RSB2	V10	IO112RSB2	
R16	GDA1/IO88PPB1	V11	IO110RSB2	
R18	GDB0/IO87NPB1	V12	IO108RSB2	
R19	GDC0/IO86NPB1	V13	IO102RSB2	
T1	IO148PPB3	V14	GND	
T2	GEC0/IO146NPB3	V15	IO93RSB2	
T4	GEB0/IO145NPB3	V16	GDA2/IO89RSB2	
T5	IO132RSB2	V17	TDI	
Т6	IO136RSB2	V18	VCCIB2	
T7	IO130RSB2	V19	TDO	
Т8	IO126RSB2	W1	GND	
Т9	IO120RSB2	W2	FF/GEB2/IO142RSB2	
T10	GND	W3	IO139RSB2	
T11	IO113RSB2	W4	IO137RSB2	
T12	IO104RSB2	W5	IO134RSB2	
T13	IO101RSB2	W6	IO133RSB2	
T14	IO98RSB2	W7	IO128RSB2	
T15	GDC2/IO91RSB2	W8	IO124RSB2	
T16	TMS	W9	IO119RSB2	
T18	VJTAG	W10	VCCIB2	
T19	GDB1/IO87PPB1	W11	IO109RSB2	
U1	IO147PDB3	W12	IO107RSB2	
U2	GEA1/IO144PPB3	W13	IO105RSB2	
U6	IO131RSB2	W14	IO100RSB2	
U14	IO99RSB2	W15	IO96RSB2	
U18	TRST	W16	IO92RSB2	
U19	GDA0/IO88NPB1	W17	GDB2/IO90RSB2	
V1	IO147NDB3	W18	ТСК	
V2	VCCIB3	W19	GND	
V3	GEC2/IO141RSB2			
V4	IO140RSB2			
V5	IO135RSB2]		
V6	GND]		
V7	IO125RSB2]		
V8	IO122RSB2	1		

V9

IO116RSB2

QN132				
Pin Number	AGL030 Function			
C17	IO47RSB1			
C18	NC			
C19	ТСК			
C20	NC			
C21	VPUMP			
C22	VJTAG			
C23	NC			
C24	NC			
C25	NC			
C26	GDB0/IO34RSB0			
C27	NC			
C28	VCCIB0			
C29	IO28RSB0			
C30	IO25RSB0			
C31	IO24RSB0			
C32	IO21RSB0			
C33	NC			
C34	NC			
C35	VCCIB0			
C36	IO13RSB0			
C37	IO10RSB0			
C38	IO07RSB0			
C39	IO03RSB0			
C40	IO00RSB0			
D1	GND			
D2	GND			
D3	GND			
D4	GND			

FG144				
Pin Number	AGL600 Function			
K1	GEB0/IO145NDB3			
K2	GEA1/IO144PDB3			
K3	GEA0/IO144NDB3			
K4	GEA2/IO143RSB2			
K5	IO119RSB2			
K6	IO111RSB2			
K7	GND			
K8	IO94RSB2			
K9	GDC2/IO91RSB2			
K10	GND			
K11	GDA0/IO88NDB1			
K12	GDB0/IO87NDB1			
L1	GND			
L2	VMV3			
L3	FF/GEB2/IO142RSB2			
L4	IO136RSB2			
L5	VCCIB2			
L6	IO115RSB2			
L7	IO103RSB2			
L8	IO97RSB2			
L9	TMS			
L10	VJTAG			
L11	VMV2			
L12	TRST			
M1	GNDQ			
M2	GEC2/IO141RSB2			
M3	IO138RSB2			
M4	IO123RSB2			
M5	IO126RSB2			
M6	IO134RSB2			
M7	IO108RSB2			
M8	IO99RSB2			
M9	TDI			
M10	VCCIB2			
M11	VPUMP			
M12	GNDQ			

FG256				
Pin Number AGL400 Function				
R5	IO123RSB2			
R6	IO118RSB2			
R7	IO112RSB2			
R8	IO106RSB2			
R9	IO100RSB2			
R10	IO96RSB2			
R11	IO89RSB2			
R12	IO85RSB2			
R13	GDB2/IO81RSB2			
R14	TDI			
R15	NC			
R16	TDO			
T1	GND			
T2	IO126RSB2			
Т3	FF/GEB2/IO133RSB2			
T4	IO124RSB2			
T5	IO116RSB2			
T6	IO113RSB2			
T7	IO107RSB2			
Т8	IO105RSB2			
Т9	IO102RSB2			
T10	IO97RSB2			
T11	IO92RSB2			
T12	GDC2/IO82RSB2			
T13	IO86RSB2			
T14	GDA2/IO80RSB2			
T15	TMS			
T16	GND			

FG256		FG256		FG256	
Pin Number	AGL600 Function	Pin Number	AGL600 Function	Pin Number	AGL600 Function
H3	GFB1/IO163PPB3	K9	GND	M15	GDC1/IO86PDB1
H4	VCOMPLF	K10	GND	M16	IO84NDB1
H5	GFC0/IO164NPB3	K11	VCC	N1	IO150NDB3
H6	VCC	K12	VCCIB1	N2	IO147PPB3
H7	GND	K13	IO73NPB1	N3	GEC1/IO146PPB3
H8	GND	K14	IO80NPB1	N4	IO140RSB2
H9	GND	K15	IO74NPB1	N5	GNDQ
H10	GND	K16	IO72NDB1	N6	GEA2/IO143RSB2
H11	VCC	L1	IO159NDB3	N7	IO126RSB2
H12	GCC0/IO69NPB1	L2	IO156NPB3	N8	IO120RSB2
H13	GCB1/IO70PPB1	L3	IO151PPB3	N9	IO108RSB2
H14	GCA0/IO71NPB1	L4	IO158PSB3	N10	IO103RSB2
H15	IO67NPB1	L5	VCCIB3	N11	IO99RSB2
H16	GCB0/IO70NPB1	L6	GND	N12	GNDQ
J1	GFA2/IO161PPB3	L7	VCC	N13	IO92RSB2
J2	GFA1/IO162PDB3	L8	VCC	N14	VJTAG
J3	VCCPLF	L9	VCC	N15	GDC0/IO86NDB1
J4	IO160NDB3	L10	VCC	N16	GDA1/IO88PDB1
J5	GFB2/IO160PDB3	L11	GND	P1	GEB1/IO145PDB3
J6	VCC	L12	VCCIB1	P2	GEB0/IO145NDB3
J7	GND	L13	GDB0/IO87NPB1	P3	VMV2
J8	GND	L14	IO85NDB1	P4	IO138RSB2
J9	GND	L15	IO85PDB1	P5	IO136RSB2
J10	GND	L16	IO84PDB1	P6	IO131RSB2
J11	VCC	M1	IO150PDB3	P7	IO124RSB2
J12	GCB2/IO73PPB1	M2	IO151NPB3	P8	IO119RSB2
J13	GCA1/IO71PPB1	M3	IO147NPB3	P9	IO107RSB2
J14	GCC2/IO74PPB1	M4	GEC0/IO146NPB3	P10	IO104RSB2
J15	IO80PPB1	M5	VMV3	P11	IO97RSB2
J16	GCA2/IO72PDB1	M6	VCCIB2	P12	VMV1
K1	GFC2/IO159PDB3	M7	VCCIB2	P13	TCK
K2	IO161NPB3	M8	IO117RSB2	P14	VPUMP
K3	IO156PPB3	M9	IO110RSB2	P15	TRST
K4	IO129RSB2	M10	VCCIB2	P16	GDA0/IO88NDB1
K5	VCCIB3	M11	VCCIB2	R1	GEA1/IO144PDB3
K6	VCC	M12	VMV2	R2	GEA0/IO144NDB3
K7	GND	M13	IO94RSB2	R3	IO139RSB2
K8	GND	M14	GDB1/IO87PPB1	R4	GEC2/IO141RSB2

IGLOO Low Power Flash FPGAs

Pin Number	AGL600 Function	Pin Number
A1	GND	AA15
A2	GND	AA16
A3	VCCIB0	AA17
A4	NC	AA18
A5	NC	AA19
A6	IO09RSB0	AA20
A7	IO15RSB0	AA21
A8	NC	AA22
A9	NC	AB1
A10	IO22RSB0	AB2
A11	IO23RSB0	AB3
A12	IO29RSB0	AB4
A13	IO35RSB0	AB5
A14	NC	AB6
A15	NC	AB7
A16	IO46RSB0	AB8
A17	IO48RSB0	AB9
A18	NC	AB10
A19	NC	AB11
A20	VCCIB0	AB12
A21	GND	AB13
A22	GND	AB14
AA1	GND	AB15
AA2	VCCIB3	AB16
AA3	NC	AB17
AA4	NC	AB18
AA5	NC	AB19
AA6	IO135RSB2	AB20
AA7	IO133RSB2	AB21
AA8	NC	AB22
AA9	NC	B1
AA10	NC	B2
AA11	NC	B3
AA12	NC	B4
AA13	NC	B5
AA14	NC	B6

FG484						
Number	AGL600 Function	Pir				
AA15	NC					
AA16	IO101RSB2					
AA17	NC					
AA18	NC					
AA19	NC					
AA20	NC					
AA21	VCCIB1					
AA22	GND					
AB1	GND					
AB2	GND					
AB3	VCCIB2					
AB4	NC					
AB5	NC					
AB6	IO130RSB2					
AB7	IO128RSB2					
AB8	IO122RSB2					
AB9	IO116RSB2					
AB10	NC					
AB11	NC					
AB12	IO113RSB2					
AB13	IO112RSB2					
AB14	NC					
AB15	NC					
AB16	IO100RSB2					
AB17	IO95RSB2					
AB18	NC					
AB19	NC					
AB20	VCCIB2					
AB21	GND					
AB22	GND					
B1	GND					
B2	VCCIB3					
B3	NC					
B4	NC					
B5	NC					
B6	IO08RSB0					

FG484	
Pin Number	AGL600 Function
B7	IO12RSB0
B8	NC
B9	NC
B10	IO17RSB0
B11	NC
B12	NC
B13	IO36RSB0
B14	NC
B15	NC
B16	IO47RSB0
B17	IO49RSB0
B18	NC
B19	NC
B20	NC
B21	VCCIB1
B22	GND
C1	VCCIB3
C2	NC
C3	NC
C4	NC
C5	GND
C6	NC
C7	NC
C8	VCC
C9	VCC
C10	NC
C11	NC
C12	NC
C13	NC
C14	VCC
C15	VCC
C16	NC
C17	NC
C18	GND
C19	NC
C20	NC

FG484	
Pin Number	AGL600 Function
Y7	NC
Y8	VCC
Y9	VCC
Y10	NC
Y11	NC
Y12	NC
Y13	NC
Y14	VCC
Y15	VCC
Y16	NC
Y17	NC
Y18	GND
Y19	NC
Y20	NC
Y21	NC
Y22	VCCIB1

FG484	
Pin Number	AGL1000 Function
A1	GND
A2	GND
A3	VCCIB0
A4	IO07RSB0
A5	IO09RSB0
A6	IO13RSB0
A7	IO18RSB0
A8	IO20RSB0
A9	IO26RSB0
A10	IO32RSB0
A11	IO40RSB0
A12	IO41RSB0
A13	IO53RSB0
A14	IO59RSB0
A15	IO64RSB0
A16	IO65RSB0
A17	IO67RSB0
A18	IO69RSB0
A19	NC
A20	VCCIB0
A21	GND
A22	GND
AA1	GND
AA2	VCCIB3
AA3	NC
AA4	IO181RSB2
AA5	IO178RSB2
AA6	IO175RSB2
AA7	IO169RSB2
AA8	IO166RSB2
AA9	IO160RSB2
AA10	IO152RSB2
AA11	IO146RSB2
AA12	IO139RSB2
AA13	IO133RSB2
AA14	NC

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